

IN THE SPECIFICATION

Please replace the paragraph 122 with the following rewritten paragraph:

B2
-- [0122] FIG. 24 shows a sectional view of another preferred embodiment of a biosensor unit 800 representing a preferred embodiment of a plurality of biosensors 810 positioned on a substrate 805 housing semiconductor components 820 as shown in FIG. 23. As seen in FIG. 24, the biosensor unit 800 comprises a CMOS and/or BJT layer 830, an electrochemical layer 840 and a reagent containment layer 850, and is generally similar to the FIG. 22 embodiment already described. --

Please replace the paragraph 125 with the following rewritten paragraph:

B3
-- [0125] Referring now to FIG. 26, a second silicon dioxide layer (5000 .ANG.) 920 is next deposited on the substrate 900 for electrical isolation. Referring now to FIG. 27, the second silicon dioxide layer 920 is then selectively etched by using lithography and etching methods to form an electric connection hole 940. Referring now to FIG. 28, a conducting plug 950 is then applied into the contact hole 940. Conducting plug 950 is used as interconnection between conductive electrode 960 with low resistance source 917 and/or drain 919. --

Please replace the paragraph 126 with the following rewritten paragraph:

B4
-- [0126] FIG. 29 shows a lift-off process for the fabrication of the necessary electrodes. The electrodes for biosensing are patterned on substrate 900 by using PR5214 photo resist layer 970 on the second silicon dioxide layer 920. Next, a mask 921 is used to transfer a desired pattern onto photo resist layer 970 by using reverse imaging process (which includes the removal of unwanted photo resist layer 970). A layer 960 of gold Au(2000 .ANG.) and/or Cr(200 .ANG.) is electron-beam deposited on the second silicon dioxide layer 920 with the desired photo resist pattern layer 970. Lastly, referring to FIG. 30, any photo resist 970 and unwanted Au/Cr 960 are removed by dissolving the photo resist pattern layer 970. --